

## General Description

The 810252I is a high performance, low jitter/low phase noise VCXO. The 810252I uses a low frequency and low cost pullable crystal to achieve jitter attenuation for synchronous Ethernet applications. The 810252I can take an input of 25MHz and produce two LVCMOS outputs of 25MHz.

The device is packaged in a small 16 lead TSSOP package and is ideal for use on space constrained boards typically encountered in most synchronous ethernet applications.

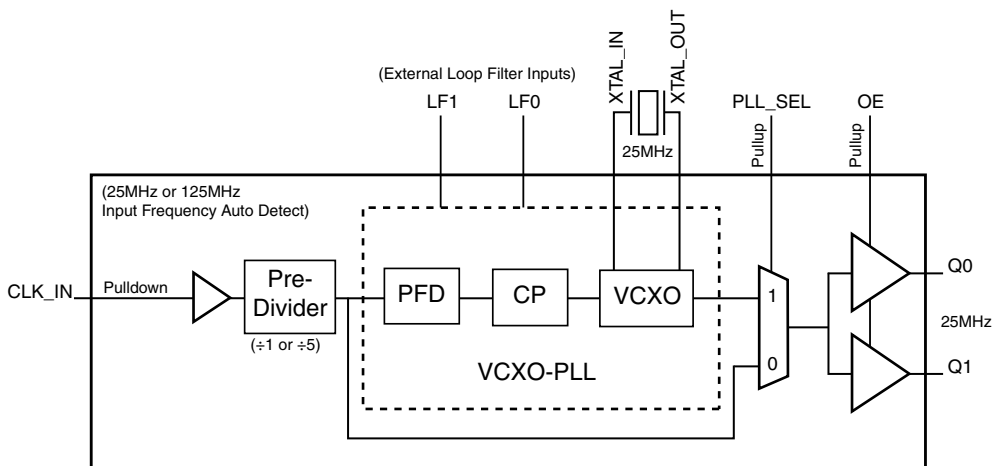
## Applications

- Synchronous Ethernet v0.39a
- End equipment compliant with Std IEEE 802.039a

## Features

- Two single-ended outputs (LVCMOS or LVTTL levels), output Impedance: 15Ω
- Phase jitter attenuation by the VCXO-PLL using a 25MHz pullable external crystal (XTAL)
- Input frequencies: 25MHz or 125MHz
- Output frequency: 25MHz
- PLL loop bandwidth adjustable by external components
- Full 3.3V or 2.5V supply voltage
- -40°C to 85°C ambient operating temperature
- Available in lead-free (RoHS 6) package

## Block Diagram



## Pin Assignment

PLL_SEL	1	16	CLK_IN
GND	2	15	VDD
Q0	3	14	LF1
Q1	4	13	LF0
VDDO	5	12	GND
OE	6	11	XTAL_IN
VDDA	7	10	XTAL_OUT
VDD	8	9	GND

### 810252I

16-Lead TSSOP  
4.4mm x 5.0mm x 0.925mm  
package body  
G Package  
Top View

**Table 1. Pin Descriptions**

Number	Name	Type		Description
1	PLL_SEL	Input	Pullup	When logic HIGH, the VCXO-PLL is enabled. When LOW, the VCXO-PLL is in bypass mode. LVCMOS/LVTTL interface levels.
2, 9, 12	GND	Power		Power supply ground.
3, 4	Q0, Q1	Output		Single-ended clock outputs. LVCMOS/ LVTTL interface levels.
5	V <sub>DDO</sub>	Power		Output power supply pin.
6	OE	Input	Pullup	Output enable pin for Qx outputs. LVCMOS/LVTTL interface levels.
7	V <sub>DDA</sub>	Power		Analog supply pin.
8, 15	V <sub>DD</sub>	Power		Core supply pins.
10, 11	XTAL_OUT, XTAL_IN	Input		VCXO crystal oscillator interface. XTAL_IN is the input. XTAL_OUT is the output.
13, 14	LF0, LF1	Analog Input/ Output		Loop filter connection node pins.
16	CLK_IN	Input	Pulldown	Single-ended clock input. LVCMOS/LVTTL interface levels.

NOTE: *Pullup* and *Pulldown* refer to internal input resistors. See Table 2, *Pin Characteristics*, for typical values.

**Table 2. Pin Characteristics**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
C <sub>IN</sub>	Input Capacitance			4		pF
C <sub>PD</sub>	Power Dissipation Capacitance	V <sub>DD</sub> , V <sub>DDO</sub> = 3.465V		8		pF
		V <sub>DD</sub> , V <sub>DDO</sub> = 2.625V		5		pF
R <sub>PULLUP</sub>	Input Pullup Resistor			51		kΩ
R <sub>PULLDOWN</sub>	Input Pulldown Resistor			51		kΩ
R <sub>OUT</sub>	Output Impedance	V <sub>DDO</sub> = 3.3V±5%		15		Ω
		V <sub>DDO</sub> = 2.5V±5%		20		Ω

## Absolute Maximum Ratings

NOTE: Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the *DC Characteristics* or *AC Characteristics* is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.

Item	Rating
Supply Voltage, $V_{DD}$	4.6V
Inputs, $V_I$ XTAL_IN Other Inputs	0V to $V_{DD}$ -0.5V to $V_{DD} + 0.5V$
Outputs, $V_O$	-0.5V to $V_{DD} + 0.5V$
Package Thermal Impedance, $\theta_{JA}$	81.2°C/W (0 mps)
Storage Temperature, $T_{STG}$	-65°C to 150°C

## DC Electrical Characteristics

**Table 3A. Power Supply DC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		3.135	3.3	3.465	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.07$	3.3	$V_{DD}$	V
$V_{DDO}$	Output Supply Voltage		3.135	3.3	3.465	V
$I_{DD}$	Power Supply Current				40	mA
$I_{DDA}$	Analog Supply Current				7	mA
$I_{DDO}$	Output Supply Current	No Load			5	mA

**Table 3B. Power Supply DC Characteristics,  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^\circ\text{C}$  to  $85^\circ\text{C}$**

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$V_{DD}$	Core Supply Voltage		2.375	2.5	2.625	V
$V_{DDA}$	Analog Supply Voltage		$V_{DD} - 0.07$	2.5	$V_{DD}$	V
$V_{DDO}$	Output Supply Voltage		2.375	2.5	2.625	V
$I_{DD}$	Power Supply Current				35	mA
$I_{DDA}$	Analog Supply Current				7	mA
$I_{DDO}$	Output Supply Current	No Load			5	mA

**Table 3C. LVCMOS/LVTTL DC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter		Test Conditions	Minimum	Typical	Maximum	Units
$V_{IH}$	Input High Voltage		$V_{DD} = 3.465V$	2		$V_{DD} + 0.3$	V
			$V_{DD} = 2.625V$	1.7		$V_{DD} + 0.3$	V
$V_{IL}$	Input Low Voltage		$V_{DD} = 3.465V$	-0.3		0.8	V
			$V_{DD} = 2.625V$	-0.3		0.7	V
$I_{IH}$	Input High Current	CLK_IN	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			150	$\mu A$
		OE, PLL_SEL	$V_{DD} = V_{IN} = 3.465V$ or $2.625V$			5	$\mu A$
$I_{IL}$	Input Low Current	CLK_IN	$V_{DD} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$	-5			$\mu A$
		OE, PLL_SEL	$V_{DD} = 3.465V$ or $2.625V$ , $V_{IN} = 0V$	-150			$\mu A$
$V_{OH}$	Output High Voltage; NOTE 1		$V_{DDO} = 3.3V \pm 5\%$	2.6			V
			$V_{DDO} = 2.5V \pm 5\%$	1.8			V
$V_{OL}$	Output Low Voltage; NOTE 1		$V_{DDO} = 3.3V \pm 5\%$			0.6	V
			$V_{DDO} = 2.5V \pm 5\%$			0.5	V

NOTE 1: Outputs terminated with  $50\Omega$  to  $V_{DDO}/2$ . See Parameter Measurement Information section. *Load Test Circuit diagrams.*

## AC Electrical Characteristics

**Table 4A. AC Characteristics,  $V_{DD} = V_{DDO} = 3.3V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{REF}$	Input Reference Frequency			25		MHz
				125		MHz
$f_{VCO}$	VCXO-PLL Frequency			25		MHz
$f_{OUT}$	Output Frequency			25		MHz
$t_{JIT(CC)}$	Cycle-to-Cycle Jitter; NOTE 1				25	ps
$t_{sk(o)}$	Output Skew; NOTE 2, 3				15	ps
$t_{jit(\theta)}$	RMS Phase Jitter (Random); NOTE 4	$f_{OUT} = 25MHz$ , Integration Range: 12kHz – 5MHz		0.25		ps
$t_{JIT(PER)}$	Period Jitter, RMS				2.7	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	550		1100	ps
odc	Output Duty Cycle; NOTE 5		48		52	%
odc	Output Duty Cycle; NOTE 6		45		55	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized using a 537Hz VCXO-PLL Loop Bandwidth. Refer to VCXO\_PLL Applications Section.

NOTE 1: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO}/2$ .

NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 4: Refer to the Phase Noise Plot.

NOTE 5: Specified with the VCXO-PLL free running high.

NOTE 6: Specified with the VCXO-PLL locked.

**Table 4B. AC Characteristics,  $V_{DD} = V_{DDO} = 2.5V \pm 5\%$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$** 

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
$f_{REF}$	Input Reference Frequency			25		MHz
				125		MHz
$f_{VCO}$	VCXO-PLL Frequency			25		MHz
$f_{OUT}$	Output Frequency			25		MHz
$t_{JIT(CC)}$	Cycle-to-Cycle Jitter; NOTE 1				20	ps
$t_{sk(o)}$	Output Skew; NOTE 2, 3				25	ps
$t_{jit}$	RMS Phase Jitter (Random); NOTE 4	$f_{OUT} = 25MHz$ , Integration Range: 12kHz – 5MHz		0.26		ps
$t_{JIT(PER)}$	Period Jitter, RMS				5.7	ps
$t_R / t_F$	Output Rise/Fall Time	20% to 80%	700		1850	ps
odc	Output Duty Cycle; NOTE 5		48		52	%
odc	Output Duty Cycle; NOTE 6		44		56	%

NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when device is mounted in a test socket with maintained transverse airflow greater than 500 lfm. Device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized using a 537Hz VCXO-PLL Loop Bandwidth. Refer to VCXO\_PLL Applications Section.

NOTE 1: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 2: Defined as skew between outputs at the same supply voltage and with equal load conditions. Measured at  $V_{DDO}/2$ .

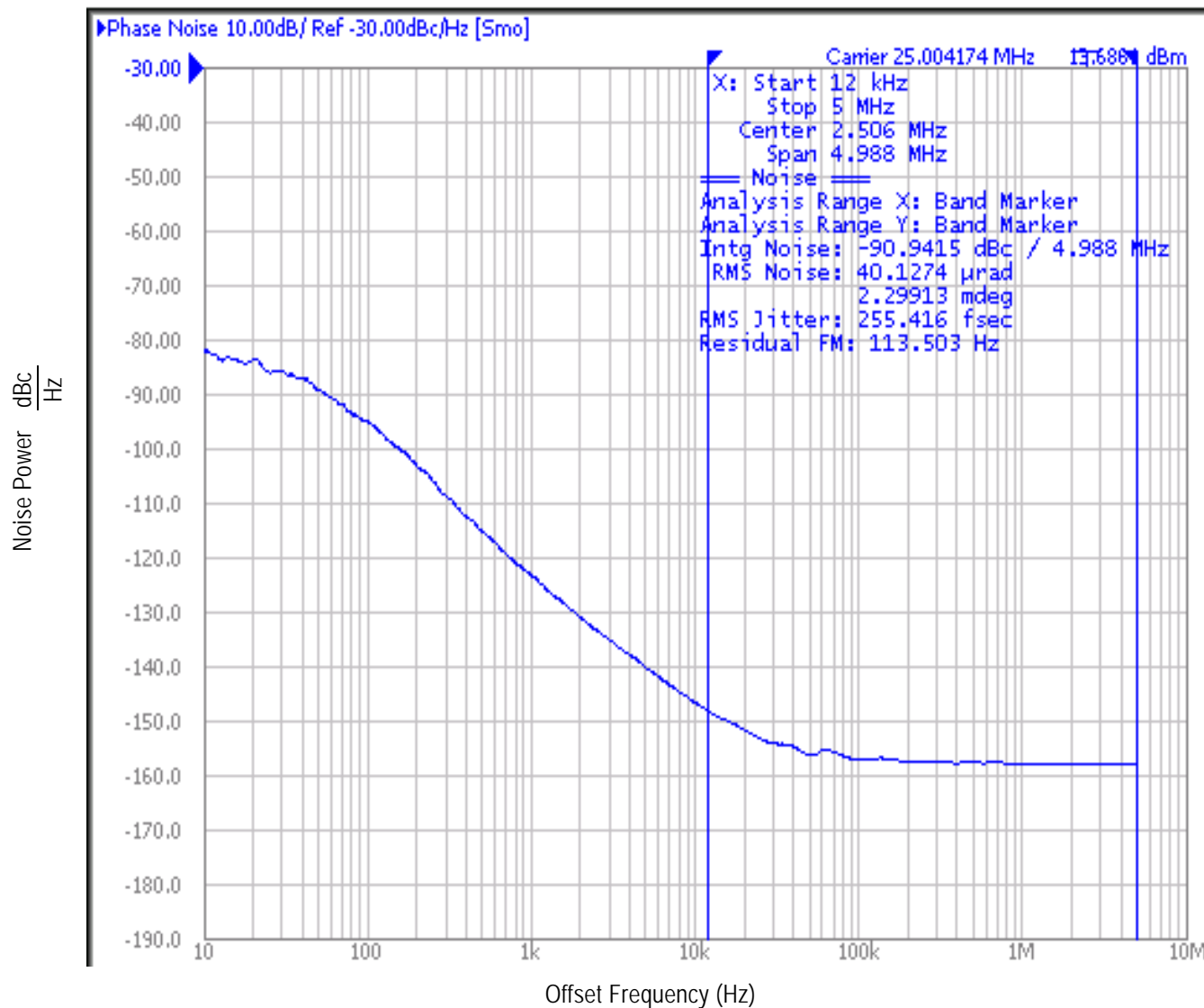
NOTE 3: This parameter is defined in accordance with JEDEC Standard 65.

NOTE 4: Refer to the Phase Noise Plot.

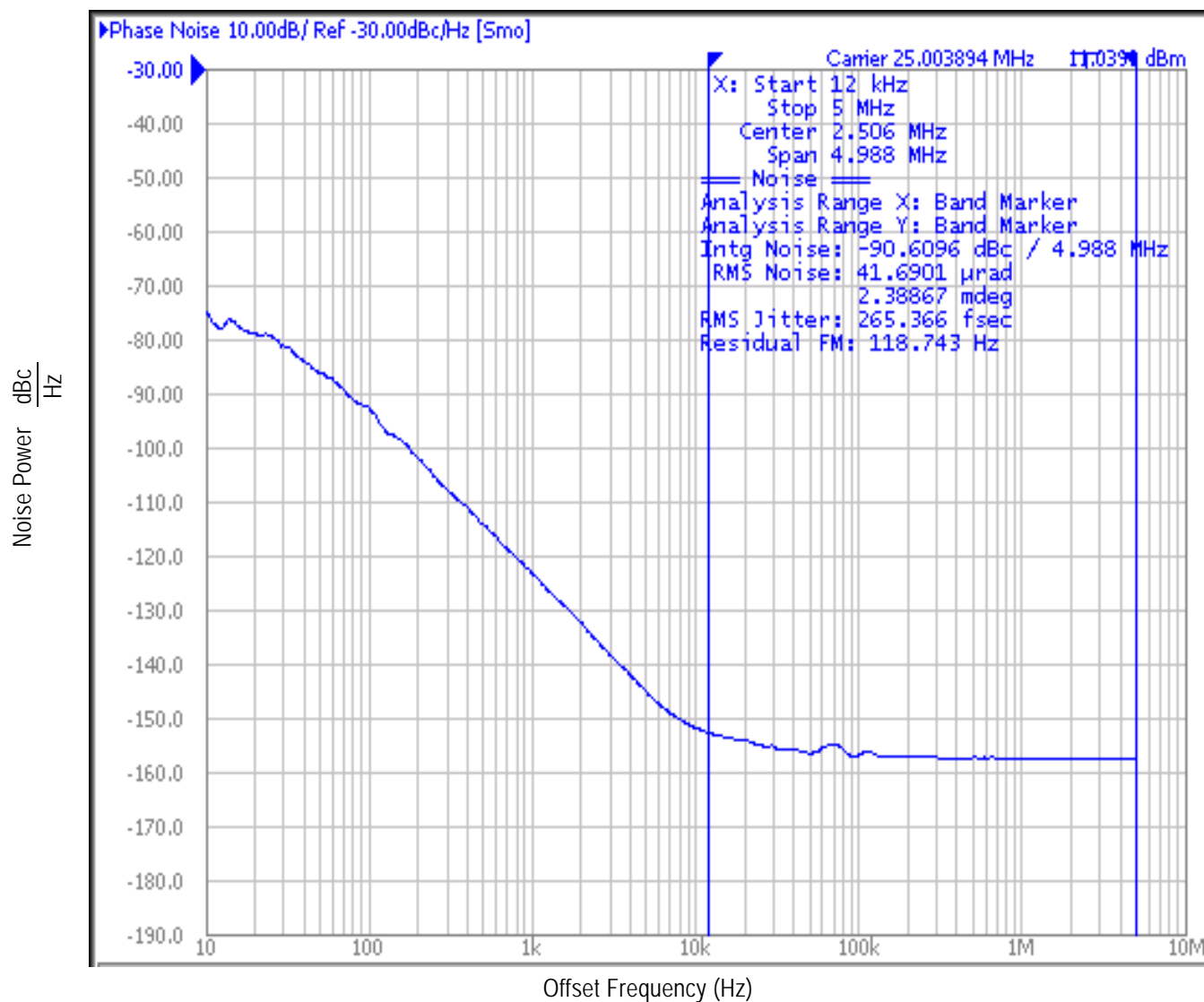
NOTE 5: Specified with the VCXO-PLL free running high.

NOTE 6: Specified with the VCXO-PLL locked.

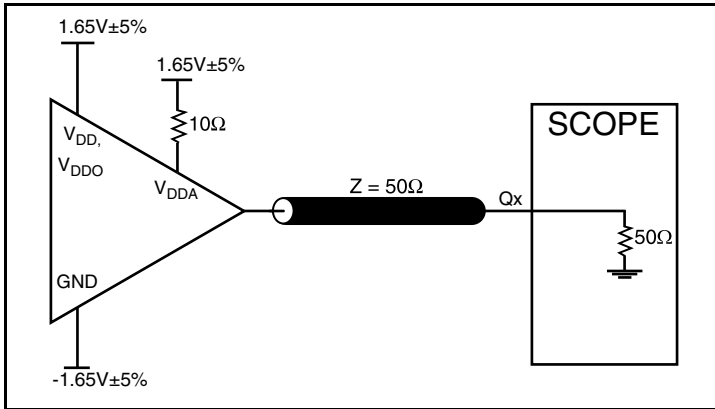
## Typical Phase Noise (3.3V)



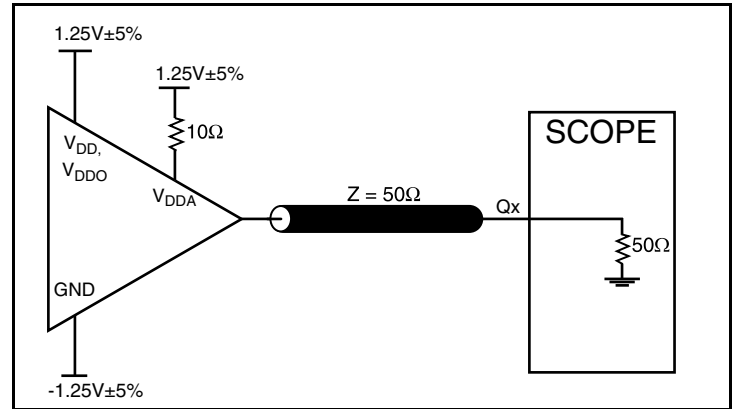
## Typical Phase Noise (2.5V)



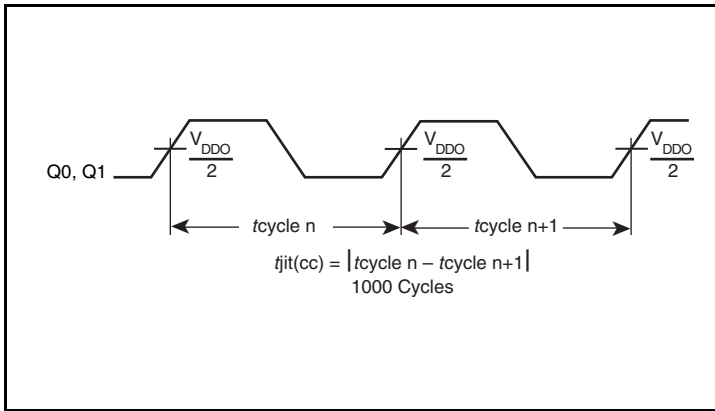
## Parameter Measurement Information



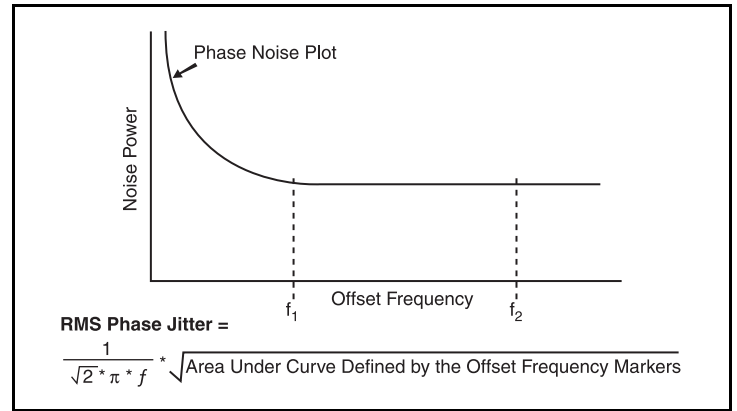
3.3V Core/3.3V LVCMOS Output Load AC Test Circuit



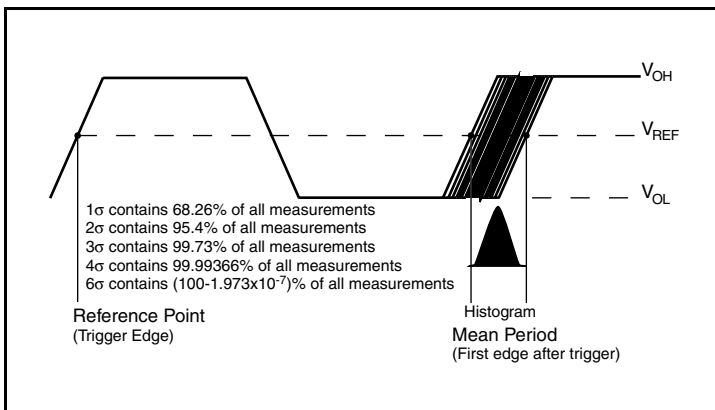
2.5V Core/2.5V LVCMOS Output Load AC Test Circuit



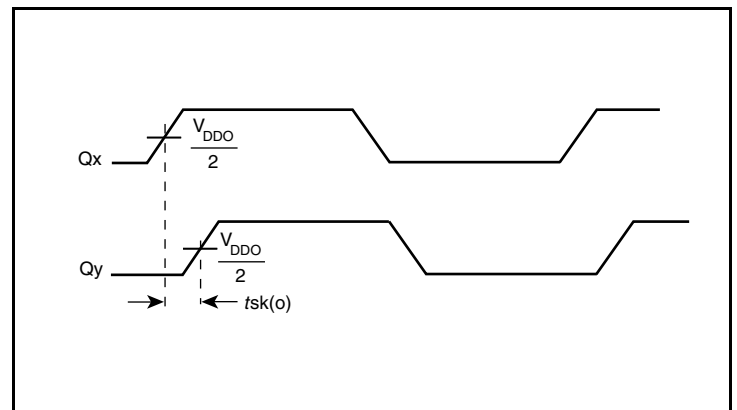
Cycle-to-Cycle Jitter



RMS Phase Jitter



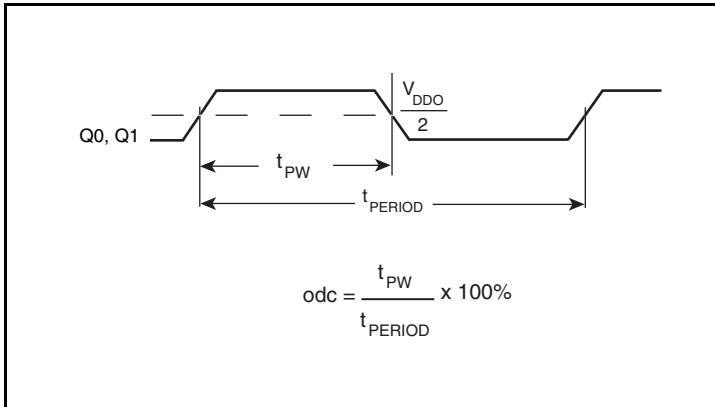
Period Jitter



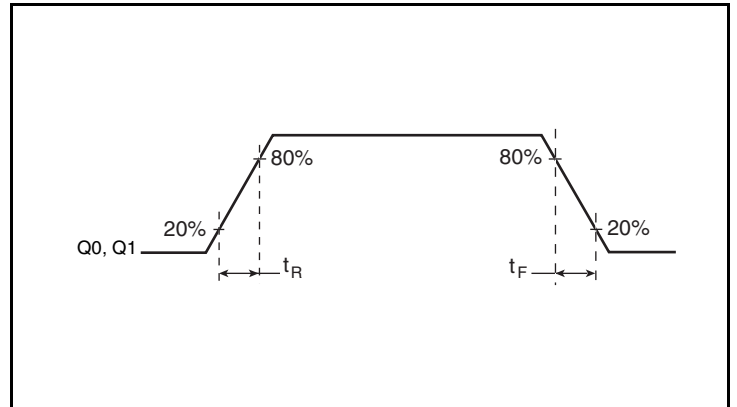
Output Skew



## Parameter Measurement Information, continued



Output Duty Cycle/Pulse Width/Period



Output Rise/Fall Time

## Application Information

### Recommendations for Unused Input Pins

#### Inputs:

##### LVC MOS Control Pins

All control pins have internal pullups; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

#### Outputs:

##### LVC MOS Outputs

All unused LVC MOS outputs can be left floating. There should be no trace attached.



## VCXO-PLL EXTERNAL COMPONENTS

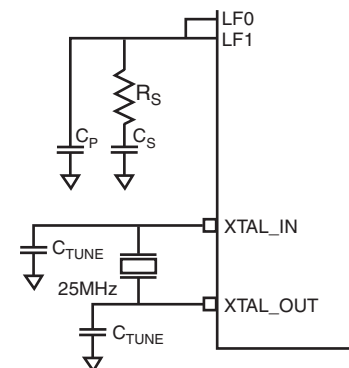
Choosing the correct external components and having a proper printed circuit board (PCB) layout is a key task for quality operation of the VCXO-PLL. In choosing a crystal, special precaution must be taken with the package and load capacitance ( $C_L$ ). In addition, frequency, accuracy and temperature range must also be considered. Since the pulling range of a crystal also varies with the package, it is recommended that a metal-canned package like HC49 be used. Generally, a metal-canned package has a larger pulling range than a surface mounted device (SMD). For crystal selection information, refer to the *VCXO Crystal Selection Application Note*.

The crystal's load capacitance  $C_L$  characteristic determines its resonating frequency and is closely related to the VCXO tuning range. The total external capacitance seen by the crystal when installed on a board is the sum of the stray board capacitance, IC package lead capacitance, internal varactor capacitance and any installed tuning capacitors ( $C_{TUNE}$ ).

If the crystal  $C_L$  is greater than the total external capacitance, the VCXO will oscillate at a higher frequency than the crystal specification. If the crystal  $C_L$  is lower than the total external capacitance, the VCXO will oscillate at a lower frequency than the crystal specification. In either case, the absolute tuning range is reduced. The correct value of  $C_L$  is dependant on the characteristics of the VCXO. The recommended  $C_L$  in the *Crystal Parameter Table* balances the tuning range by centering the tuning curve.

The frequency of oscillation in the third overtone mode is not necessarily at exactly three times the fundamental frequency. The mechanical properties of the quartz element dictate the position of the overtones relative to the fundamental. The oscillator circuit may excite both the fundamental and overtone modes simultaneously. This will cause a nonlinearity in the tuning curve. This potential problem is why VCXO crystals are required to be tested for absence of any activity inside a  $\pm 200$  ppm window at three times the fundamental frequency. Refer to  $F_{L\_3OVT}$  and  $F_{L\_3OVT\_spurs}$  in the crystal Characteristics table.

The crystal and external loop filter components should be kept as close as possible to the device. Loop filter and crystal traces should be kept short and separated from each other. Other signal traces should be kept separate and not run underneath the device, loop filter or crystal components.



### VCXO Characteristics Table

Symbol	Parameter	Typical	Units
$k_{VCXO}$	VCXO Gain	15000	Hz/V
$C_{V\_LOW}$	Low Varactor Capacitance	9.8	pF
$C_{V\_HIGH}$	High Varactor Capacitance	22.7	pF

### VCXO-PLL Loop Bandwidth Selection Table

Bandwidth	Crystal Frequency (MHz)	$R_S$ (k $\Omega$ )	$C_S$ ( $\mu$ F)	$C_P$ ( $\mu$ F)
215Hz (Low)	25	0.4	10	0.01
537Hz (Mid)	25	1.0	10	0.001
886Hz (High)	25	1.65	10	0.001

### Crystal Characteristics

Symbol	Parameter	Test Conditions	Minimum	Typical	Maximum	Units
	Mode of Oscillation		Fundamental			
$f_N$	Frequency			25		MHz
$f_T$	Frequency Tolerance				$\pm 20$	ppm
$f_S$	Frequency Stability				$\pm 20$	ppm
	Operating Temperature Range		-40		+85	$^{\circ}$ C
$C_L$	Load Capacitance			10		pF
$C_O$	Shunt Capacitance			4		pF
$C_O / C_1$	Pullability Ratio			220	240	
$F_{L\_3OVT}$	3 <sup>rd</sup> Overtone $F_L$		200			ppm
$F_{L\_3OVT\_spurs}$	3 <sup>rd</sup> Overtone $F_L$ Spurs		200			ppm
ESR	Equivalent Series Resistance				20	$\Omega$
	Drive Level				1	mW
	Aging @ 25 $^{\circ}$ C	First Year			$\pm 3$	ppm
		Ten Years			$\pm 10$	ppm

## Power Considerations

This section provides information on power dissipation and junction temperature for the 810252I. Equations and example calculations are also provided.

### 1. Power Dissipation.

The total power dissipation for the 810252I is the sum of the core power plus the analog power plus the power dissipated in the load(s). The following is the power dissipation for  $V_{DD} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

- Power (core)<sub>MAX</sub> =  $V_{DD\_MAX} * (I_{DD} + I_{DDA} + I_{DDO}) = 3.465V * (40mA + 7mA + 5mA) = \mathbf{180.18mW}$
- Output Impedance  $R_{OUT}$  Power Dissipation due to Loading  $50\Omega$  to  $V_{DD}/2$   
Output Current  $I_{OUT} = V_{DD\_MAX} / [2 * (50\Omega + R_{OUT})] = 3.465V / [2 * (50\Omega + 15\Omega)] = \mathbf{26.7mA}$
- Power Dissipation on the  $R_{OUT}$  per LVCMOS output  
Power ( $R_{OUT}$ ) =  $R_{OUT} * (I_{OUT})^2 = 15\Omega * (26.7mA)^2 = \mathbf{10.7mW}$  per output
- Total Power ( $R_{OUT}$ ) =  $10.7mW * 2 = \mathbf{21.4mW}$

### Dynamic Power Dissipation at 25MHz

$$\text{Power (25MHz)} = C_{PD} * \text{Frequency} * (V_{DD})^2 = 8pF * 25MHz * (3.465V)^2 = \mathbf{2.4mW}$$
 per output

$$\text{Total Power (25MHz)} = 2.4mW * 2 = \mathbf{4.8mW}$$

### Total Power Dissipation

- Total Power**  
= Power (core)<sub>MAX</sub> + Power ( $R_{OUT}$ ) + Power (25MHz)  
=  $180.18mW + 21.4mW + 4.8mW$   
= **206.38mW**

### 2. Junction Temperature.

Junction temperature,  $T_j$ , is the temperature at the junction of the bond wire and bond pad directly affects the reliability of the device. The maximum recommended junction temperature is  $125^\circ\text{C}$ . Limiting the internal transistor junction temperature,  $T_j$ , to  $125^\circ\text{C}$  ensures that the bond wire and bond pad temperature remains below  $125^\circ\text{C}$ .

The equation for  $T_j$  is as follows:  $T_j = \theta_{JA} * Pd\_total + T_A$

$T_j$  = Junction Temperature

$\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

$Pd\_total$  = Total Device Power Dissipation (example calculation is in section 1 above)

$T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is  $81.2^\circ\text{C/W}$  per Table 5 below.

Therefore,  $T_j$  for an ambient temperature of  $85^\circ\text{C}$  with all outputs switching is:

$$85^\circ\text{C} + 0.296W * 81.2^\circ\text{C/W} = 101.7^\circ\text{C}. \text{ This is well below the limit of } 125^\circ\text{C}.$$

This calculation is only an example.  $T_j$  will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

**Table 5. Thermal Resistance  $\theta_{JA}$  for 16 Lead TSSOP, Forced Convection**

$\theta_{JA}$ by Velocity			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	$81.2^\circ\text{C/W}$	$73.9^\circ\text{C/W}$	$70.2^\circ\text{C/W}$

## Reliability Information

Table 6.  $\theta_{JA}$  vs. Air Flow Table for a 16 Lead TSSOP

$\theta_{JA}$ vs. Air Flow			
Meters per Second	0	1	2.5
Multi-Layer PCB, JEDEC Standard Test Boards	81.2°C/W	73.9°C/W	70.2°C/W

## Transistor Count

The transistor count for 810252I: 1025

## Package Outline and Package Dimensions

Package Outline - G Suffix for 16 Lead TSSOP

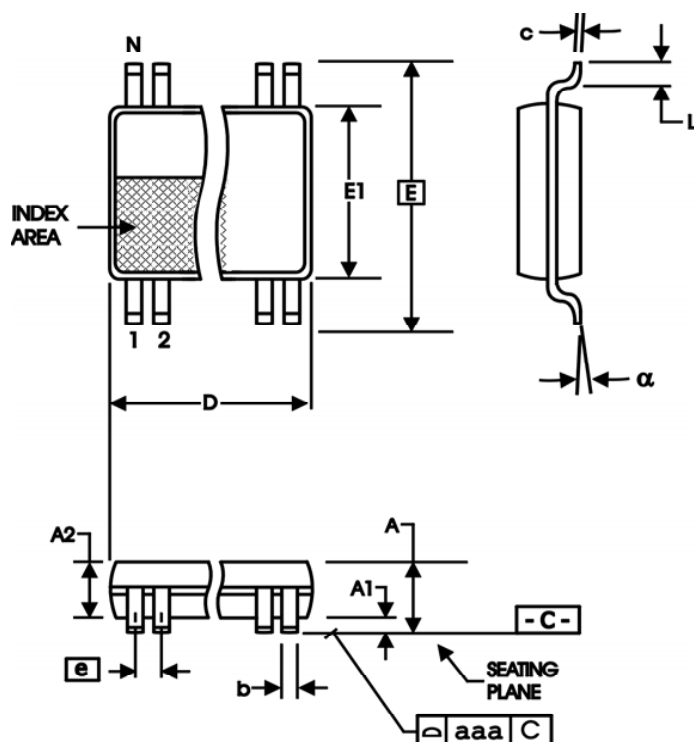


Table 7. Package Dimensions for 16 Lead TSSOP

All Dimensions in Millimeters		
Symbol	Minimum	Maximum
N	16	
A		1.20
A1	0.5	0.15
A2	0.80	1.05
b	0.19	0.30
c	0.09	0.20
D	4.90	5.10
E	6.40 Basic	
E1	4.30	4.50
e	0.65 Basic	
L	0.45	0.75
$\alpha$	0°	8°
aaa		0.10

Reference Document: JEDEC Publication 95, MO-153

## Ordering Information

Table 8. Ordering Information

Part/Order Number	Marking	Package	Shipping Packaging	Temperature
810252AGILF	10252AIL	16 Lead "Lead-Free" TSSOP	Tube	-40°C to 85°C
810252AGILFT	10252AIL	16 Lead "Lead-Free" TSSOP	Tape & Reel	-40°C to 85°C

## Revision History Sheet

Rev	Table	Page	Description of Change	Date
B	T4A	4	3.3V AC Characteristics Table - Added additional odc row with specs of 45min and 55max. Added Notes 5 & 6.	7/17/2012
	T4B	5	2.5V AC Characteristics Table - Added additional odc row with specs of 44min and 56max. Added Notes 5 & 6.	
B		1	Features List: deleted 'Absolute pull range is $\pm 80$ ppm' HiPerClock references have been deleted throughout the datasheet	8/1/12
B	T4A	4	Added 'high' to Note 5.	10/5/12
	T4B	5	Added 'high' to Note 5.	
	T8	14	Deleted quantity from Tape and Reel.	
B		15	Removed ICS from part numbers where needed. Revision history - Corrected spelling errors in section one of this table. Updated header and footer.	3/3/16





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### Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu,  
Koto-ku, Tokyo 135-0061, Japan  
[www.renesas.com](http://www.renesas.com)

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